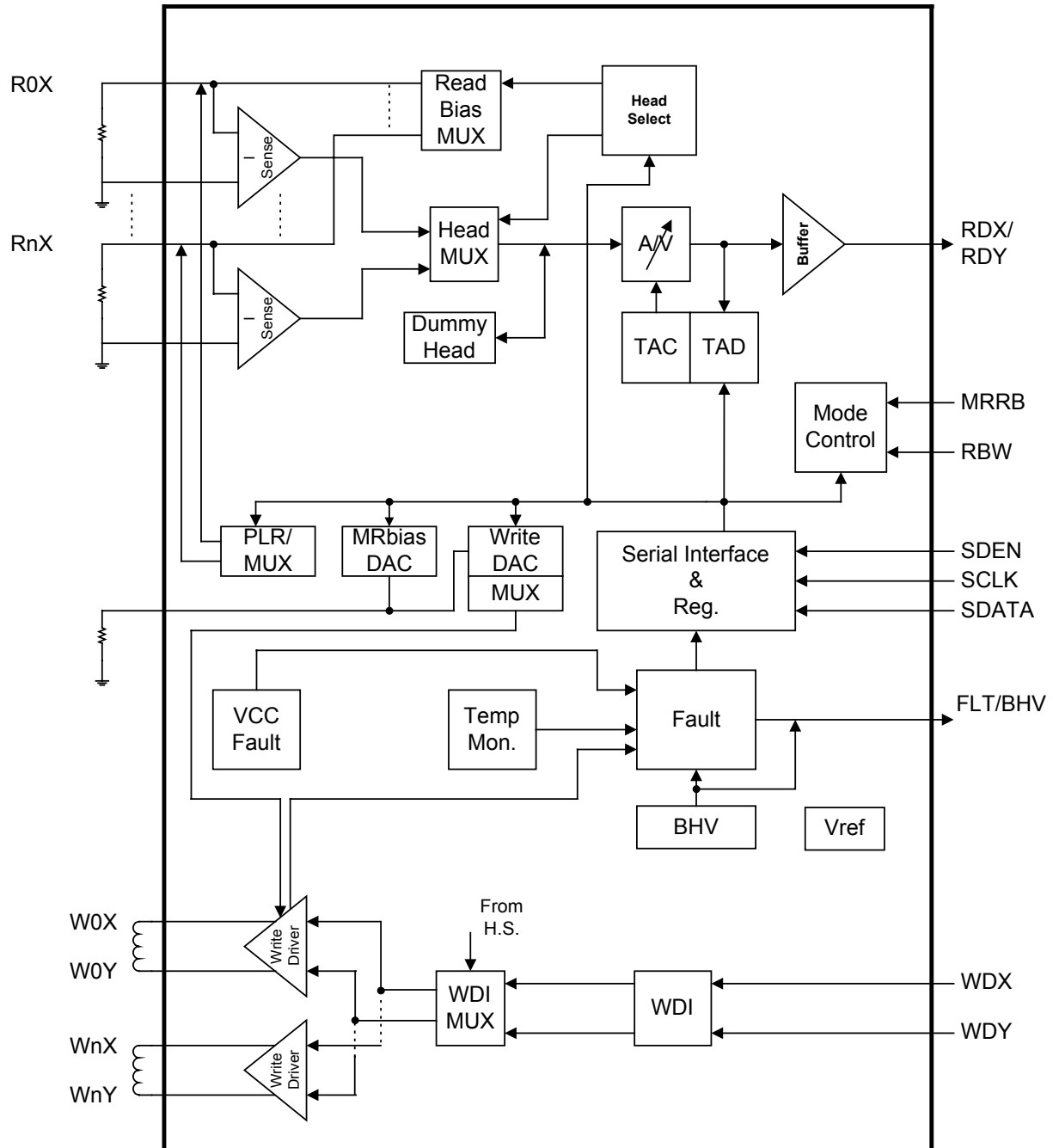


FEATURES

- Current Bias/Current Sense Architecture
- Operates from 5V supply
- Variable Power Supply from 5 to 8V for Writer High Performance Circuitry (Patent Pending)
- 3-line serial interface with readback (3.3V CMOS compatible)
- Power management modes
- On-chip temperature monitor
- Internal reference resistor (2Kohm) (External optional)
- Head unsafe fault detection for both read and write
- Unselected read/write heads at GND potential
- Fast recovery mode
- 300MHz Read Bandwidth
- One side grounded input, fully differential output
- Read frequency boost
- Programmable GMR resistance measurement mode (5-bits)
- Programmable GMR Pinned Layer Reset (PLR) pulse circuit
- GMR bias current range 2-9.75 mA (5-bits)
- GMR resistor range = 25 to 75 Ω
- Programmable read gain = 225 V/V or 300 V/V
- Input equivalent noise TBD $nV\sqrt{Hz}$ @ $R_{mr} = 45\Omega$
- TA detection & programmable compensation
- 1.7ns Write rise/fall time ($L=90$ nH/40 mA)
- Variable Power Supply from 5 to 8V for high performance Writer Circuitry up to Rise/Fall Time: 0.5 ns Typical ($I_w = 40$ mA (0-p), $L_{tf} = 60$ nH, $R_{tf} = 15 \Omega$)
- Write current range = 15-60 mA (5-bits)
- Programmable write current overshoot (4-bits)
- Programmable write current undershoot (3-bit)
- 200ns Write/Read switching time
- Servo write (half bank or all bank write)



LD3500 Block Diagram